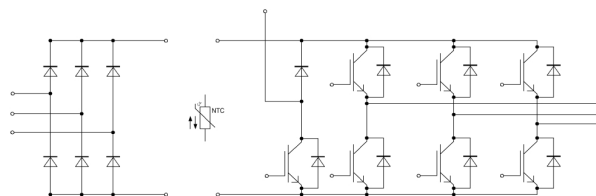
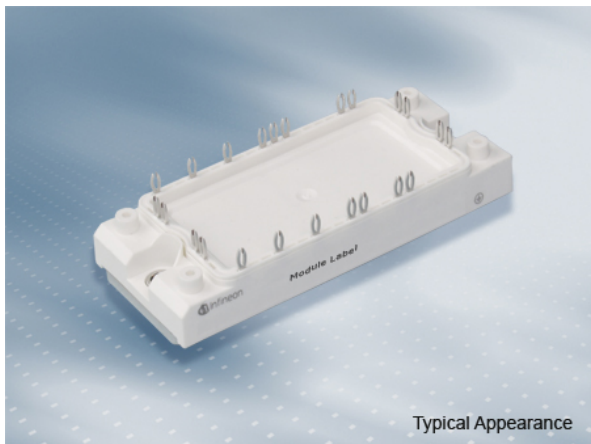


EconoPIM™2 モジュール トレンチ/フィールドストップ IGBT4 and エミッターコントロール4 diode内蔵 and PressFIT / NTCサーミスタ

EconoPIM™2 module with Trench/Fieldstop IGBT4 and Emitter Controlled 4 diode and PressFIT / NTC

暫定データ / Preliminary Data



$V_{CES} = 1200V$
 $I_{C\ nom} = 25A / I_{CRM} = 50A$

一般応用

- モーター駆動
- サーボ駆動

Typical Applications

- Motor Drives
- Servo Drives

電気的特性

- 拡張された動作温度 $T_{vj\ op}$
- 低スイッチング損失
- トレンチ IGBT 4
- $T_{vj\ op} = 150^{\circ}C$

Electrical Features

- Extended Operation Temperature $T_{vj\ op}$
- Low Switching Losses
- Trench IGBT 4
- $T_{vj\ op} = 150^{\circ}C$

機械的特性

- 高いパワー/サーマルサイクル耐量
- 内蔵されたNTCサーミスタ
- 絶縁されたベースプレート
- 銅ベースプレート
- PressFIT 接合 技術
- RoHS対応
- 標準ハウジング

Mechanical Features

- High Power and Thermal Cycling Capability
- Integrated NTC temperature sensor
- Isolated Base Plate
- Copper Base Plate
- PressFIT Contact Technology
- RoHS compliant
- Standard Housing

Module Label Code

Barcode Code 128



DMX - Code



Content of the Code

Content of the Code	Digit
Module Serial Number	1 - 5
Module Material Number	6 - 11
Production Order Number	12 - 19
Datecode (Production Year)	20 - 21
Datecode (Production Week)	22 - 23

prepared by: AS	date of publication: 2013-11-25	
approved by: RS	revision: 2.0	UL approved (E83335)



暫定データ
Preliminary Data

IGBT- インバータ / IGBT, Inverter
最大定格 / Maximum Rated Values

コレクタ・エミッタ間電圧 Collector-emitter voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{CES}	1200	V
連続DCコレクタ電流 Continuous DC collector current	$T_C = 100^{\circ}\text{C}, T_{vj\max} = 175^{\circ}\text{C}$	$I_{C\text{nom}}$	25	A
繰り返しピークコレクタ電流 Repetitive peak collector current	$t_P = 1\text{ms}$	I_{CRM}	50	A
トータル損失 Total power dissipation	$T_C = 25^{\circ}\text{C}, T_{vj\max} = 175^{\circ}\text{C}$	P_{tot}	160	W
ゲート・エミッタ間ピーク電圧 Gate-emitter peak voltage		V_{GES}	+/-20	V

電気的特性 / Characteristic Values

			min.	typ.	max.	
コレクタ・エミッタ間飽和電圧 Collector-emitter saturation voltage	$I_C = 25\text{A}, V_{GE} = 15\text{V}$ $I_C = 25\text{A}, V_{GE} = 15\text{V}$ $I_C = 25\text{A}, V_{GE} = 15\text{V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$V_{CE\text{sat}}$	1,85 2,15 2,25	2,15	V V V
ゲート・エミッタ間しきい値電圧 Gate threshold voltage	$I_C = 0,80\text{mA}, V_{CE} = V_{GE}, T_{vj} = 25^{\circ}\text{C}$		V_{GEth}	5,2 5,8	6,4	V
ゲート電荷量 Gate charge	$V_{GE} = -15\text{V} \dots +15\text{V}$		Q_G	0,20		μC
内蔵ゲート抵抗 Internal gate resistor	$T_{vj} = 25^{\circ}\text{C}$		R_{Gint}	0,0		Ω
入力容量 Input capacitance	$f = 1\text{MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{V}, V_{GE} = 0\text{V}$		C_{ies}	1,45		nF
帰還容量 Reverse transfer capacitance	$f = 1\text{MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{V}, V_{GE} = 0\text{V}$		C_{res}	0,05		nF
コレクタ・エミッタ間遮断電流 Collector-emitter cut-off current	$V_{CE} = 1200\text{V}, V_{GE} = 0\text{V}, T_{vj} = 25^{\circ}\text{C}$		I_{CES}		1,0	mA
ゲート・エミッタ間漏れ電流 Gate-emitter leakage current	$V_{CE} = 0\text{V}, V_{GE} = 20\text{V}, T_{vj} = 25^{\circ}\text{C}$		I_{GES}		100	nA
ターンオン遅れ時間 (誘導負荷) Turn-on delay time, inductive load	$I_C = 25\text{A}, V_{CE} = 600\text{V}$ $V_{GE} = \pm 15\text{V}$ $R_{Gon} = 18\Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_{don}	0,16 0,17 0,17		μs μs μs
ターンオン上昇時間 (誘導負荷) Rise time, inductive load	$I_C = 25\text{A}, V_{CE} = 600\text{V}$ $V_{GE} = \pm 15\text{V}$ $R_{Gon} = 18\Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_r	0,03 0,04 0,04		μs μs μs
ターンオフ遅れ時間 (誘導負荷) Turn-off delay time, inductive load	$I_C = 25\text{A}, V_{CE} = 600\text{V}$ $V_{GE} = \pm 15\text{V}$ $R_{Goff} = 18\Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_{doff}	0,33 0,43 0,45		μs μs μs
ターンオフ下降時間 (誘導負荷) Fall time, inductive load	$I_C = 25\text{A}, V_{CE} = 600\text{V}$ $V_{GE} = \pm 15\text{V}$ $R_{Goff} = 18\Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_f	0,08 0,15 0,17		μs μs μs
ターンオンスイッチング損失 Turn-on energy loss per pulse	$I_C = 25\text{A}, V_{CE} = 600\text{V}, L_S = 20\text{nH}$ $V_{GE} = \pm 15\text{V}, di/dt = 900\text{A}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $R_{Gon} = 18\Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{on}	1,80 2,40 2,65		mJ mJ mJ
ターンオフスイッチング損失 Turn-off energy loss per pulse	$I_C = 25\text{A}, V_{CE} = 600\text{V}, L_S = 20\text{nH}$ $V_{GE} = \pm 15\text{V}, du/dt = 3600\text{V}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $R_{Goff} = 18\Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{off}	1,40 2,20 2,40		mJ mJ mJ
短絡電流 SC data	$V_{GE} \leq 15\text{V}, V_{CC} = 800\text{V}$ $V_{CE\text{max}} = V_{CES} - L_{SCE} \cdot di/dt$ $t_P \leq 10\mu\text{s}, T_{vj} = 150^{\circ}\text{C}$		I_{SC}	90		A
ジャンクション・ケース間熱抵抗 Thermal resistance, junction to case	IGBT部 (1素子当り) / per IGBT		R_{thJC}		0,95	K/W
ケース・ヒートシンク間熱抵抗 Thermal resistance, case to heatsink	IGBT部 (1素子当り) / per IGBT $\lambda_{\text{Paste}} = 1\text{W}/(\text{m}\cdot\text{K})$ / $\lambda_{\text{grease}} = 1\text{W}/(\text{m}\cdot\text{K})$		R_{thCH}	0,36		K/W
動作温度 Temperature under switching conditions			$T_{vj\text{op}}$	-40	150	$^{\circ}\text{C}$

prepared by: AS	date of publication: 2013-11-25
approved by: RS	revision: 2.0



暫定データ
Preliminary Data

Diode、インバータ / Diode, Inverter
最大定格 / Maximum Rated Values

ピーク繰返し逆電圧 Repetitive peak reverse voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{RRM}	1200	V
連続DC電流 Continuous DC forward current		I_F	25	A
ピーク繰返し順電流 Repetitive peak forward current	$t_p = 1\text{ ms}$	I_{FRM}	50	A
電流二乗時間積 I^2t - value	$V_R = 0\text{ V}, t_p = 10\text{ ms}, T_{vj} = 125^{\circ}\text{C}$ $V_R = 0\text{ V}, t_p = 10\text{ ms}, T_{vj} = 150^{\circ}\text{C}$	I^2t	90,0 75,0	A^2s A^2s

電気的特性 / Characteristic Values

			min.	typ.	max.	
順電圧 Forward voltage	$I_F = 25\text{ A}, V_{GE} = 0\text{ V}$ $I_F = 25\text{ A}, V_{GE} = 0\text{ V}$ $I_F = 25\text{ A}, V_{GE} = 0\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	V_F	1,75 1,75 1,75	2,15	V V V
ピーク逆回復電流 Peak reverse recovery current	$I_F = 25\text{ A}, -di_F/dt = 900\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 600\text{ V}$ $V_{GE} = -15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	I_{RM}	48,0 50,0 52,0		A A A
逆回復電荷量 Recovered charge	$I_F = 25\text{ A}, -di_F/dt = 900\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 600\text{ V}$ $V_{GE} = -15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	Q_r	2,50 4,40 4,90		μC μC μC
逆回復損失 Reverse recovery energy	$I_F = 25\text{ A}, -di_F/dt = 900\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 600\text{ V}$ $V_{GE} = -15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{rec}	1,00 1,80 2,10		mJ mJ mJ
ジャンクション・ケース間熱抵抗 Thermal resistance, junction to case	/Diode (1 素子当り) / per diode		R_{thJC}		1,35	K/W
ケース・ヒートシンク間熱抵抗 Thermal resistance, case to heatsink	/Diode (1 素子当り) / per diode $\lambda_{Paste} = 1\text{ W}/(\text{m}\cdot\text{K})$ / $\lambda_{grease} = 1\text{ W}/(\text{m}\cdot\text{K})$		R_{thCH}	0,51		K/W
動作温度 Temperature under switching conditions			$T_{vj\text{ op}}$	-40	150	$^{\circ}\text{C}$

Diode、整流器 / Diode, Rectifier
最大定格 / Maximum Rated Values

ピーク繰返し逆電圧 Repetitive peak reverse voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{RRM}	1600	V
最大実効順電流/chip Maximum RMS forward current per chip	$T_C = 80^{\circ}\text{C}$	I_{FRMSM}	50	A
整流出力の最大実効電流 Maximum RMS current at rectifier output	$T_C = 80^{\circ}\text{C}$	I_{RMSM}	80	A
サージ順電流 Surge forward current	$t_p = 10\text{ ms}, T_{vj} = 25^{\circ}\text{C}$ $t_p = 10\text{ ms}, T_{vj} = 150^{\circ}\text{C}$	I_{FSM}	450 370	A A
電流二乗時間積 I^2t - value	$t_p = 10\text{ ms}, T_{vj} = 25^{\circ}\text{C}$ $t_p = 10\text{ ms}, T_{vj} = 150^{\circ}\text{C}$	I^2t	1000 685	A^2s A^2s

電気的特性 / Characteristic Values

			min.	typ.	max.	
順電圧 Forward voltage	$T_{vj} = 150^{\circ}\text{C}, I_F = 25\text{ A}$	V_F		0,90		V
逆電流 Reverse current	$T_{vj} = 150^{\circ}\text{C}, V_R = 1600\text{ V}$	I_R		1,00		mA
ジャンクション・ケース間熱抵抗 Thermal resistance, junction to case	/Diode (1 素子当り) / per diode	R_{thJC}			0,85	K/W
ケース・ヒートシンク間熱抵抗 Thermal resistance, case to heatsink	/Diode (1 素子当り) / per diode $\lambda_{Paste} = 1\text{ W}/(\text{m}\cdot\text{K})$ / $\lambda_{grease} = 1\text{ W}/(\text{m}\cdot\text{K})$	R_{thCH}		0,32		K/W
動作温度 Temperature under switching conditions		$T_{vj\text{ op}}$	-40		150	$^{\circ}\text{C}$

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暫定データ
Preliminary Data

IGBT-ブレーキチョッパー / IGBT, Brake-Chopper
最大定格 / Maximum Rated Values

コレクタ・エミッタ間電圧 Collector-emitter voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{CES}	1200	V
連続DCコレクタ電流 Continuous DC collector current	$T_C = 100^{\circ}\text{C}, T_{vj\max} = 175^{\circ}\text{C}$ $T_C = 25^{\circ}\text{C}, T_{vj\max} = 175^{\circ}\text{C}$	$I_{C\text{nom}}$ I_C	15 28	A A
繰り返しピークコレクタ電流 Repetitive peak collector current	$t_P = 1\text{ms}$	I_{CRM}	30	A
トータル損失 Total power dissipation	$T_C = 25^{\circ}\text{C}, T_{vj\max} = 175^{\circ}\text{C}$	P_{tot}	105	W
ゲート・エミッタ間ピーク電圧 Gate-emitter peak voltage		V_{GES}	+/-20	V

電気的特性 / Characteristic Values

			min.	typ.	max.		
コレクタ・エミッタ間飽和電圧 Collector-emitter saturation voltage	$I_C = 15\text{A}, V_{GE} = 15\text{V}$ $I_C = 15\text{A}, V_{GE} = 15\text{V}$ $I_C = 15\text{A}, V_{GE} = 15\text{V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$V_{CE\text{sat}}$	1,85 2,15 2,25	2,15	V V V	
ゲート・エミッタ間しきい値電圧 Gate threshold voltage	$I_C = 0,48\text{mA}, V_{CE} = V_{GE}, T_{vj} = 25^{\circ}\text{C}$		V_{GEth}	5,2	5,8	6,4	V
ゲート電荷量 Gate charge	$V_{GE} = -15\text{V} \dots +15\text{V}$		Q_G	0,12			μC
内蔵ゲート抵抗 Internal gate resistor	$T_{vj} = 25^{\circ}\text{C}$		R_{Gint}	0,0			Ω
入力容量 Input capacitance	$f = 1\text{MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{V}, V_{GE} = 0\text{V}$		C_{ies}	0,89			nF
帰還容量 Reverse transfer capacitance	$f = 1\text{MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{V}, V_{GE} = 0\text{V}$		C_{res}	0,03			nF
コレクタ・エミッタ間遮断電流 Collector-emitter cut-off current	$V_{CE} = 1200\text{V}, V_{GE} = 0\text{V}, T_{vj} = 25^{\circ}\text{C}$		I_{CES}			1,0	mA
ゲート・エミッタ間漏れ電流 Gate-emitter leakage current	$V_{CE} = 0\text{V}, V_{GE} = 20\text{V}, T_{vj} = 25^{\circ}\text{C}$		I_{GES}			100	nA
ターンオン遅れ時間 (誘導負荷) Turn-on delay time, inductive load	$I_C = 15\text{A}, V_{CE} = 600\text{V}$ $V_{GE} = \pm 15\text{V}$ $R_{Gon} = 43\Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_{don}	0,065 0,065 0,065			μs μs μs
ターンオン上昇時間 (誘導負荷) Rise time, inductive load	$I_C = 15\text{A}, V_{CE} = 600\text{V}$ $V_{GE} = \pm 15\text{V}$ $R_{Gon} = 43\Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_r	0,06 0,065 0,065			μs μs μs
ターンオフ遅れ時間 (誘導負荷) Turn-off delay time, inductive load	$I_C = 15\text{A}, V_{CE} = 600\text{V}$ $V_{GE} = \pm 15\text{V}$ $R_{Goff} = 43\Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_{doff}	0,21 0,28 0,285			μs μs μs
ターンオフ下降時間 (誘導負荷) Fall time, inductive load	$I_C = 15\text{A}, V_{CE} = 600\text{V}$ $V_{GE} = \pm 15\text{V}$ $R_{Goff} = 43\Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_f	0,17 0,20 0,225			μs μs μs
ターンオンスイッチング損失 Turn-on energy loss per pulse	$I_C = 15\text{A}, V_{CE} = 600\text{V}, L_S = 20\text{nH}$ $V_{GE} = \pm 15\text{V}, di/dt = 500\text{A}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $R_{Gon} = 43\Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{on}	1,35 1,80 2,00			mJ mJ mJ
ターンオフスイッチング損失 Turn-off energy loss per pulse	$I_C = 15\text{A}, V_{CE} = 600\text{V}, L_S = 20\text{nH}$ $V_{GE} = \pm 15\text{V}, du/dt = 3600\text{V}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $R_{Goff} = 43\Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{off}	0,85 1,20 1,35			mJ mJ mJ
短絡電流 SC data	$V_{GE} \leq 15\text{V}, V_{CC} = 800\text{V}$ $V_{CE\text{max}} = V_{CES} - L_{SCE} \cdot di/dt$ $t_P \leq 10\mu\text{s}, T_{vj} = 150^{\circ}\text{C}$		I_{SC}	55			A
ジャンクション・ケース間熱抵抗 Thermal resistance, junction to case	IGBT部 (1素子当り) / per IGBT		R_{thJC}			1,40	K/W
ケース・ヒートシンク間熱抵抗 Thermal resistance, case to heatsink	IGBT部 (1素子当り) / per IGBT $\lambda_{\text{Paste}} = 1\text{W}/(\text{m}\cdot\text{K})$ / $\lambda_{\text{grease}} = 1\text{W}/(\text{m}\cdot\text{K})$		R_{thCH}	0,53			K/W
動作温度 Temperature under switching conditions			$T_{vj\text{op}}$	-40		150	$^{\circ}\text{C}$

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暫定データ
Preliminary Data

Diode、ブレーキチョッパー / Diode, Brake-Chopper
最大定格 / Maximum Rated Values

ピーク繰返し逆電圧 Repetitive peak reverse voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{RRM}	1200	V
連続DC電流 Continuous DC forward current		I_F	10	A
ピーク繰返し順電流 Repetitive peak forward current	$t_P = 1\text{ ms}$	I_{FRM}	20	A
電流二乗時間積 I^2t - value	$V_R = 0\text{ V}, t_P = 10\text{ ms}, T_{vj} = 125^{\circ}\text{C}$	I^2t	16,0	A ² s

電気的特性 / Characteristic Values

			min.	typ.	max.	
順電圧 Forward voltage	$I_F = 10\text{ A}, V_{GE} = 0\text{ V}$ $I_F = 10\text{ A}, V_{GE} = 0\text{ V}$ $I_F = 10\text{ A}, V_{GE} = 0\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	V_F	1,75 1,75 1,75	2,15	V V V
ピーク逆回復電流 Peak reverse recovery current	$I_F = 10\text{ A}, -di_F/dt = 500\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 600\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	I_{RM}	12,0 10,0 8,00		A A A
逆回復電荷量 Recovered charge	$I_F = 10\text{ A}, -di_F/dt = 500\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 600\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	Q_r	0,90 1,70 1,90		μC μC μC
逆回復損失 Reverse recovery energy	$I_F = 10\text{ A}, -di_F/dt = 500\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 600\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{rec}	0,24 0,52 0,59		mJ mJ mJ
ジャンクション・ケース間熱抵抗 Thermal resistance, junction to case	/Diode (1 素子当り) / per diode		R_{thJC}		2,30	K/W
ケース・ヒートシンク間熱抵抗 Thermal resistance, case to heatsink	/Diode (1 素子当り) / per diode $\lambda_{Paste} = 1\text{ W}/(\text{m}\cdot\text{K}) / \lambda_{grease} = 1\text{ W}/(\text{m}\cdot\text{K})$		R_{thCH}	0,875		K/W
動作温度 Temperature under switching conditions			$T_{vj\text{ op}}$	-40	150	$^{\circ}\text{C}$

NTC-サーミスタ / NTC-Thermistor

電気的特性 / Characteristic Values

			min.	typ.	max.	
定格抵抗値 Rated resistance	$T_C = 25^{\circ}\text{C}$		R_{25}	5,00		k Ω
R100の偏差 Deviation of R100	$T_C = 100^{\circ}\text{C}, R_{100} = 493\ \Omega$		$\Delta R/R$	-5	5	%
損失 Power dissipation	$T_C = 25^{\circ}\text{C}$		P_{25}		20,0	mW
B-定数 B-value	$R_2 = R_{25} \exp [B_{25/50}(1/T_2 - 1/(298,15\text{ K}))]$		$B_{25/50}$	3375		K
B-定数 B-value	$R_2 = R_{25} \exp [B_{25/80}(1/T_2 - 1/(298,15\text{ K}))]$		$B_{25/80}$	3411		K
B-定数 B-value	$R_2 = R_{25} \exp [B_{25/100}(1/T_2 - 1/(298,15\text{ K}))]$		$B_{25/100}$	3433		K

適切なアプリケーションノートによる仕様
Specification according to the valid application note.

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暫定データ
Preliminary Data

モジュール / Module

絶縁耐圧 Isolation test voltage	RMS, f = 50 Hz, t = 1 min.	V _{ISOL}	2,5		kV
ベースプレート材質 Material of module baseplate			Cu		
内部絶縁 Internal isolation	基礎絶縁 (クラス1, IEC 61140) basic insulation (class 1, IEC 61140)		Al ₂ O ₃		
沿面距離 Creepage distance	連絡方法 - ヒートシンク / terminal to heatsink 連絡方法 - 連絡方法 / terminal to terminal		10,0		mm
空間距離 Clearance	連絡方法 - ヒートシンク / terminal to heatsink 連絡方法 - 連絡方法 / terminal to terminal		7,5		mm
相対トラッキング指数 Comperative tracking index		CTI	> 200		
min. typ. max.					
ケース・ヒートシンク間熱抵抗 Thermal resistance, case to heatsink	/モジュール / per module λ _{Paste} = 1 W/(m·K) / λ _{grease} = 1 W/(m·K)	R _{thCH}	0,02		K/W
内部インダクタンス Stray inductance module		L _{sCE}	60		nH
パワーターミナル・チップ間抵抗 Module lead resistance, terminals - chip	T _c = 25°C, /スイッチ / per switch	R _{CC+EE'} R _{AA+CC'}	4,00 3,00		mΩ
最大ジャンクション温度 Maximum junction temperature	インバータ、ブレーキチョッパー / inverter, brake-chopper 整流器 / rectifier	T _{vj max}			175 °C 150 °C
動作温度 Temperature under switching conditions	インバータ、ブレーキチョッパー / inverter, brake-chopper 整流器 / rectifier	T _{vj op}	-40 -40		150 °C 150 °C
保存温度 Storage temperature		T _{stg}	-40		125 °C
取り付けネジ締め付けトルク Mounting torque for modul mounting	取り付けネジ M5 適切なアプリケーションノートによるマウンティング Screw M5 - Mounting according to valid application note	M	3,00	-	6,00 Nm
質量 Weight		G		180	g

bei Betrieb mit V_{ge} = 0V/+15V empfehlen wir einen R_{gon,min} von 36 Ohm und eine R_{goff,min} von 36 Ohm (siehe AN 2006-01)
for operation with V_{ge} = 0V/+15V we recommend a R_{gon,min} of 36 ohms and a R_{goff,min} of 36 ohms (see AN 2006-01)

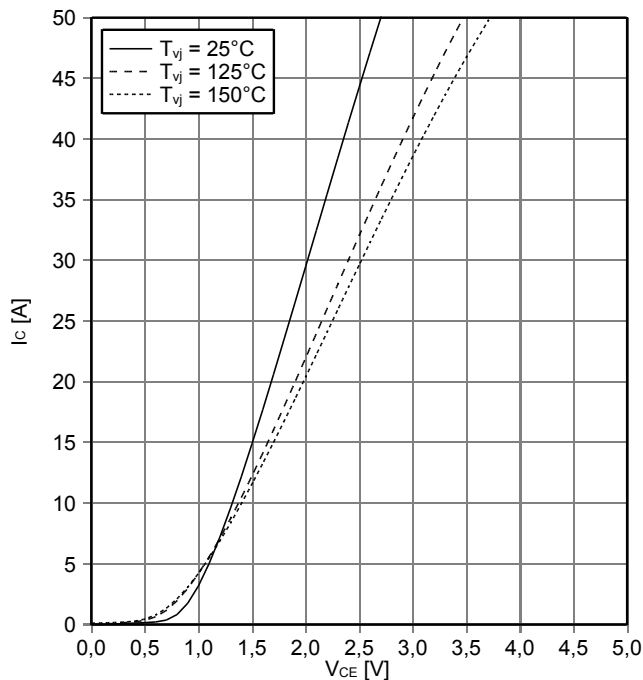
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Preliminary Data

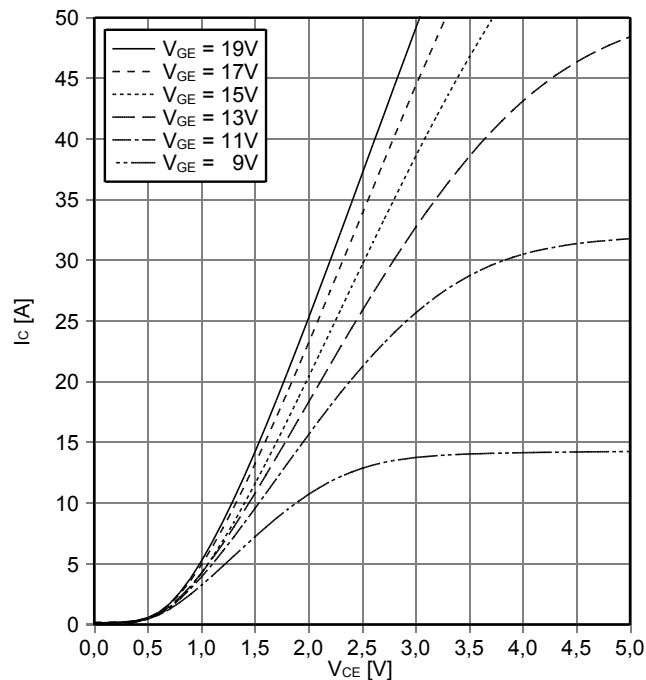
出力特性 IGBT- インバータ (Typical)
output characteristic IGBT, Inverter (typical)

$I_C = f(V_{CE})$
 $V_{GE} = 15\text{ V}$



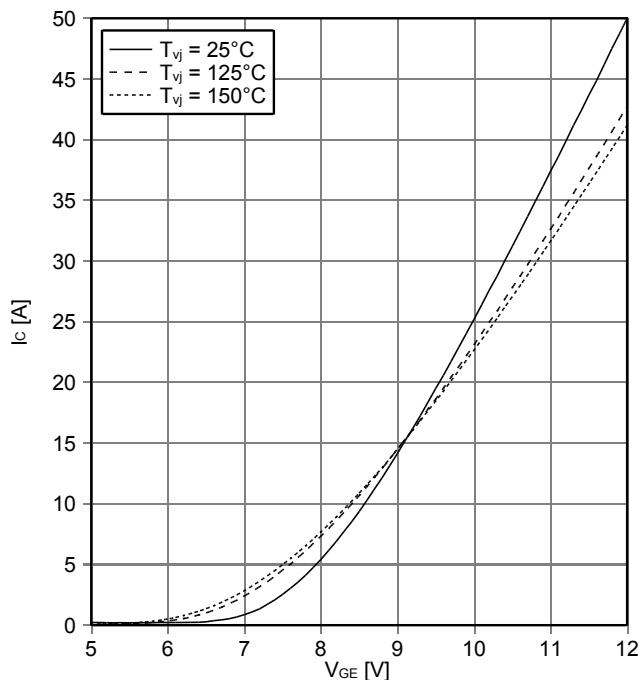
出力特性 IGBT- インバータ (Typical)
output characteristic IGBT, Inverter (typical)

$I_C = f(V_{CE})$
 $T_{vj} = 150^\circ\text{C}$



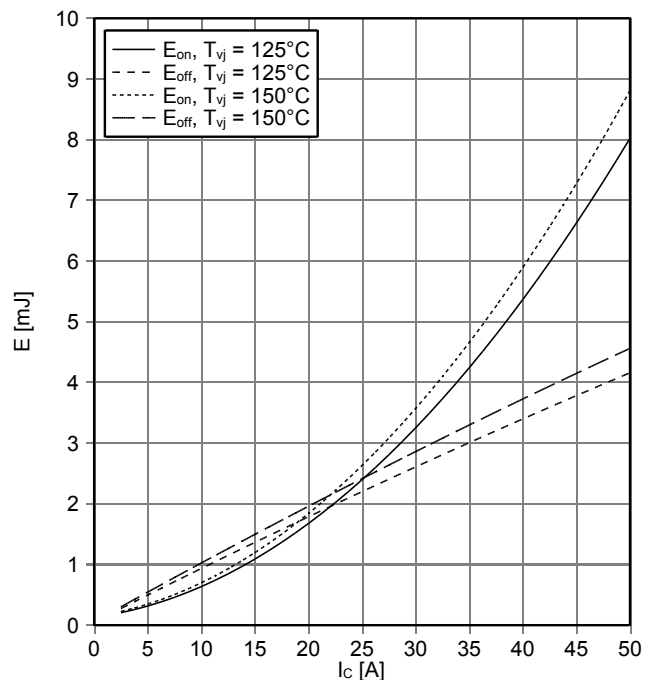
伝達特性 IGBT- インバータ (Typical)
transfer characteristic IGBT, Inverter (typical)

$I_C = f(V_{GE})$
 $V_{CE} = 20\text{ V}$



スイッチング損失 IGBT- インバータ (Typical)
switching losses IGBT, Inverter (typical)

$E_{on} = f(I_C), E_{off} = f(I_C)$
 $V_{GE} = \pm 15\text{ V}, R_{Gon} = 18\ \Omega, R_{Goff} = 18\ \Omega, V_{CE} = 600\text{ V}$



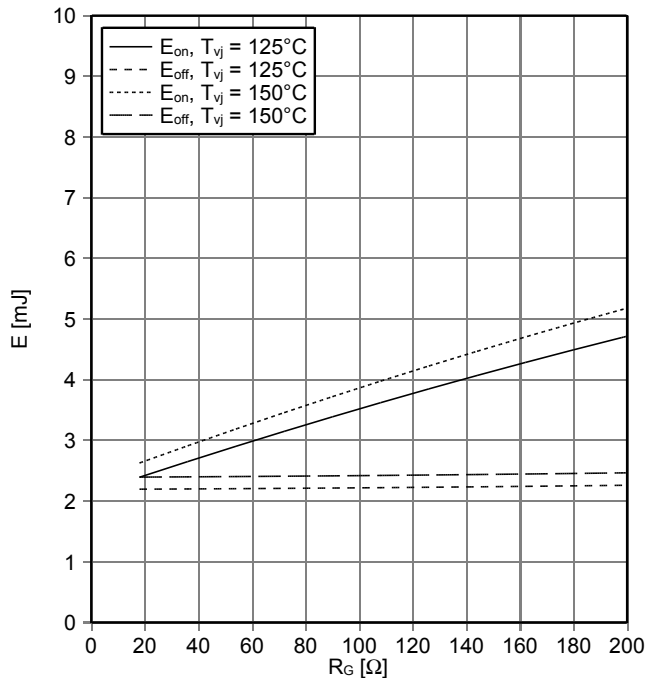
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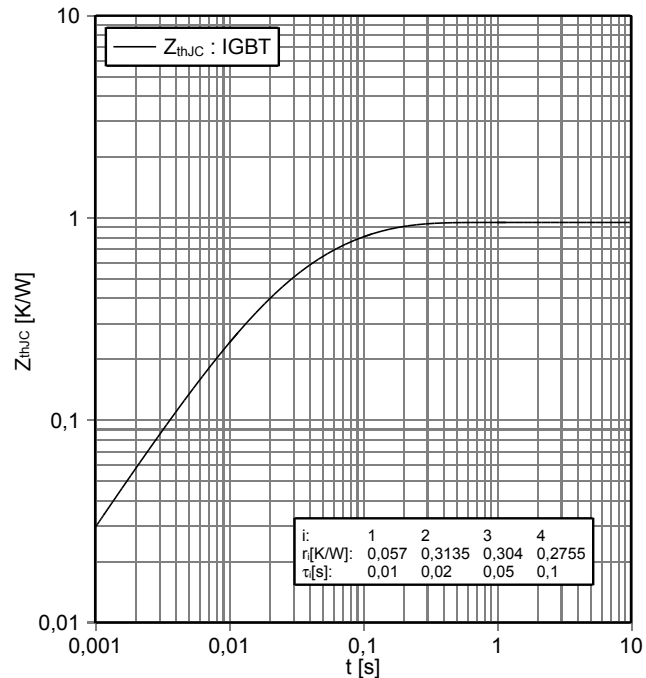
スイッチング損失 IGBT- インバータ (Typical)
switching losses IGBT, Inverter (typical)

$E_{on} = f(R_G), E_{off} = f(R_G)$
 $V_{GE} = \pm 15 V, I_C = 25 A, V_{CE} = 600 V$



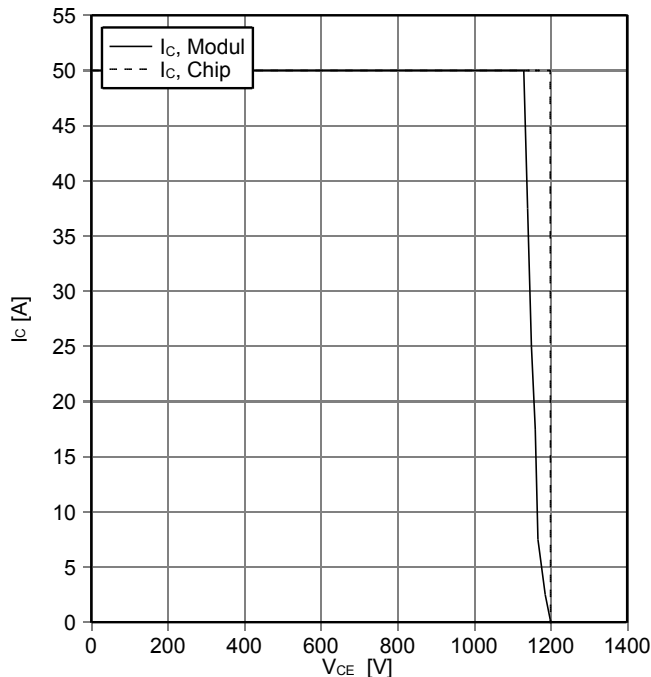
過渡熱インピーダンス IGBT- インバータ
transient thermal impedance IGBT, Inverter

$Z_{thJC} = f(t)$



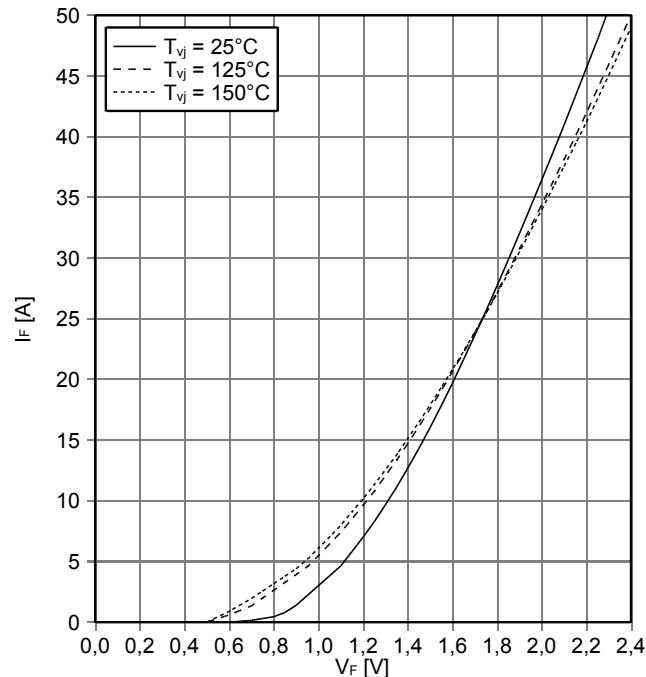
逆バイアス安全動作領域 IGBT- インバータ (RBSOA)
reverse bias safe operating area IGBT, Inverter (RBSOA)

$I_C = f(V_{CE})$
 $V_{GE} = \pm 15 V, R_{Goff} = 18 \Omega, T_{vj} = 150^\circ C$



順電圧特性 Diode、インバータ (typical)
forward characteristic of Diode, Inverter (typical)

$I_F = f(V_F)$



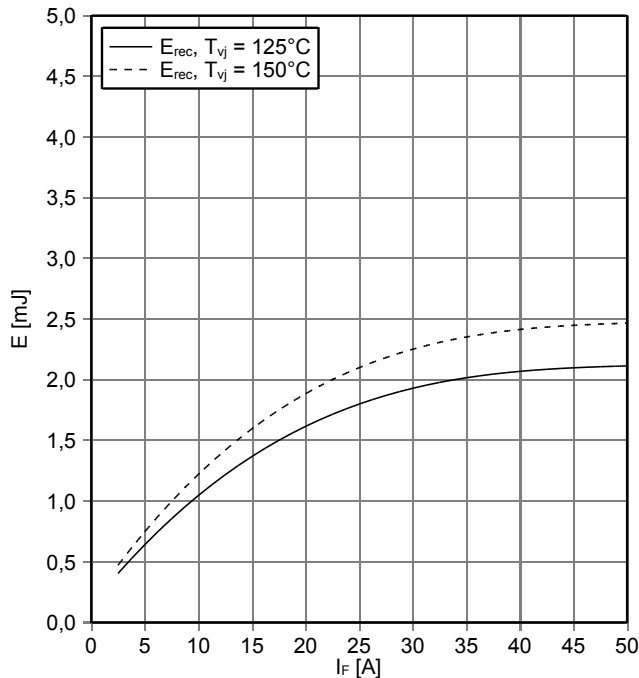
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Preliminary Data

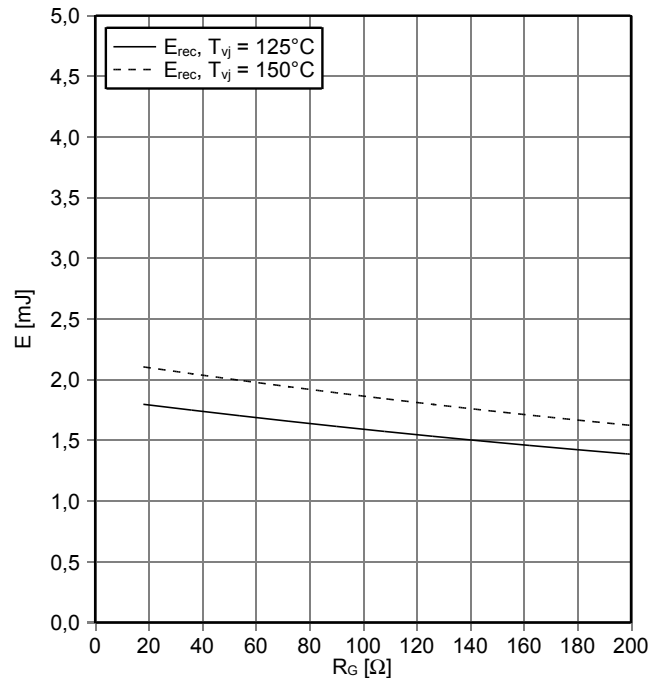
スイッチング損失 Diode、インバータ (Typical)
switching losses Diode, Inverter (typical)

$E_{rec} = f(I_F)$
 $R_{Gon} = 18 \Omega, V_{CE} = 600 V$



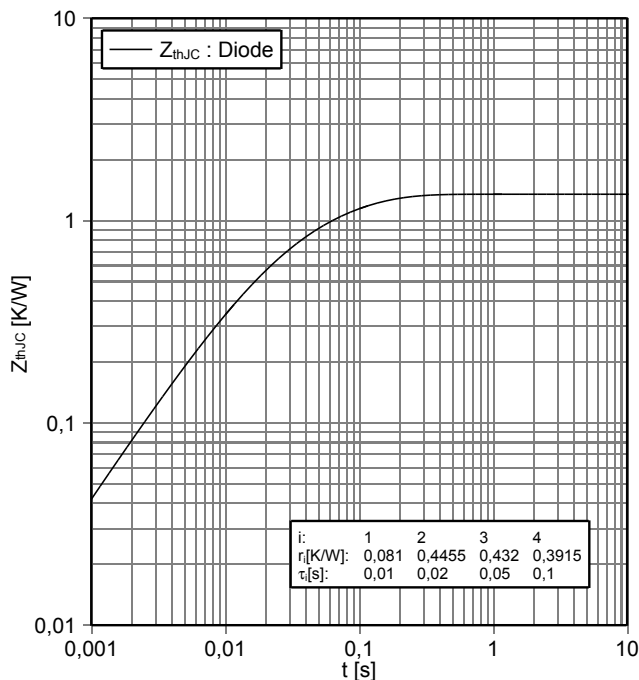
スイッチング損失 Diode、インバータ (Typical)
switching losses Diode, Inverter (typical)

$E_{rec} = f(R_G)$
 $I_F = 25 A, V_{CE} = 600 V$



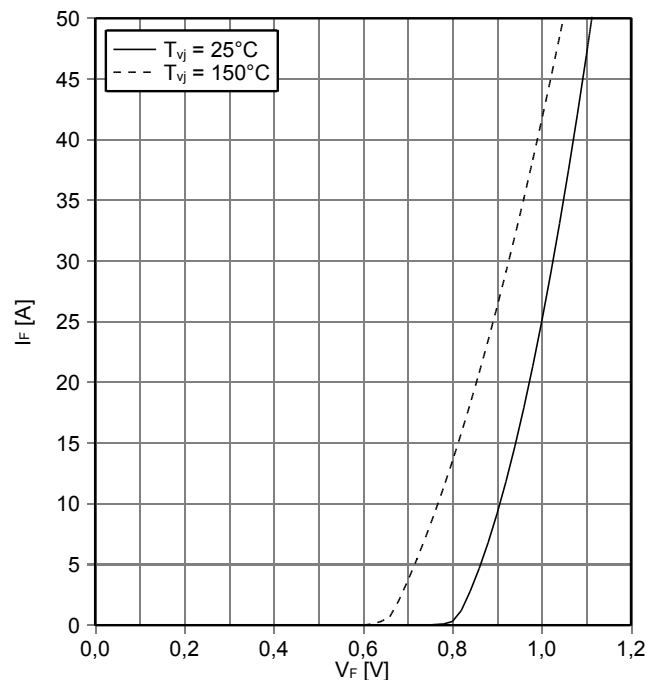
過渡熱インピーダンス Diode、インバータ
transient thermal impedance Diode, Inverter

$Z_{thJC} = f(t)$



順方向特性 Diode、整流器 (典型)
forward characteristic of Diode, Rectifier (typical)

$I_F = f(V_F)$



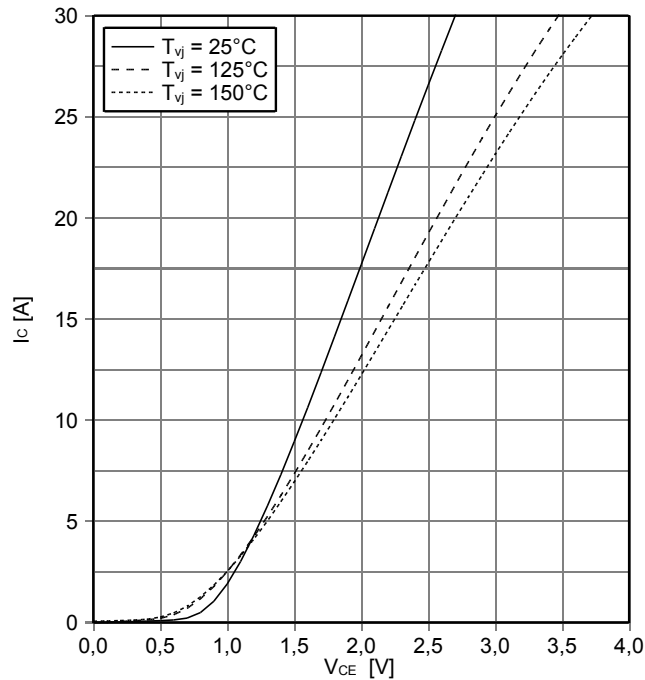
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Preliminary Data

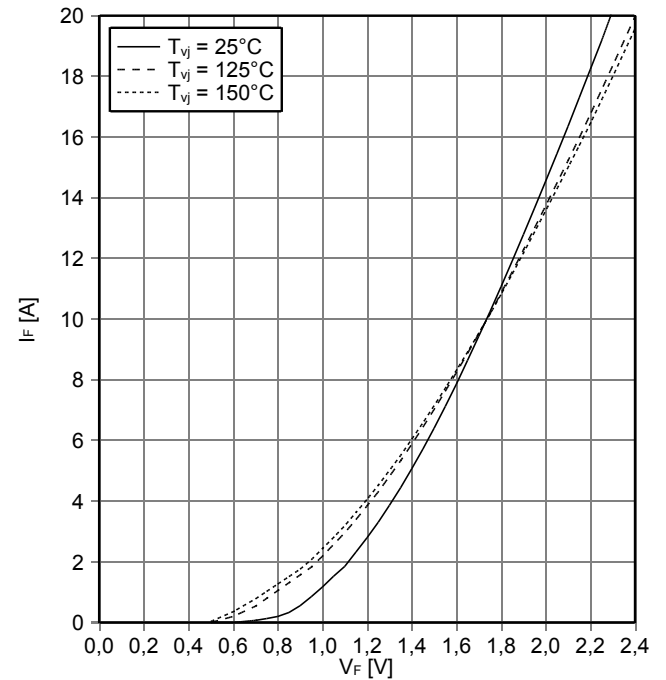
出力特性 IGBT-ブレーキチョッパー (Typical)
output characteristic IGBT, Brake-Chopper (typical)

$I_C = f(V_{CE})$
 $V_{GE} = 15\text{ V}$



順電圧特性 Diode、ブレーキチョッパー (typical)
forward characteristic of Diode, Brake-Chopper (typical)

$I_F = f(V_F)$



NTC-サーミスタ サーミスタの温度特性
NTC-Thermistor-temperature characteristic (typical)

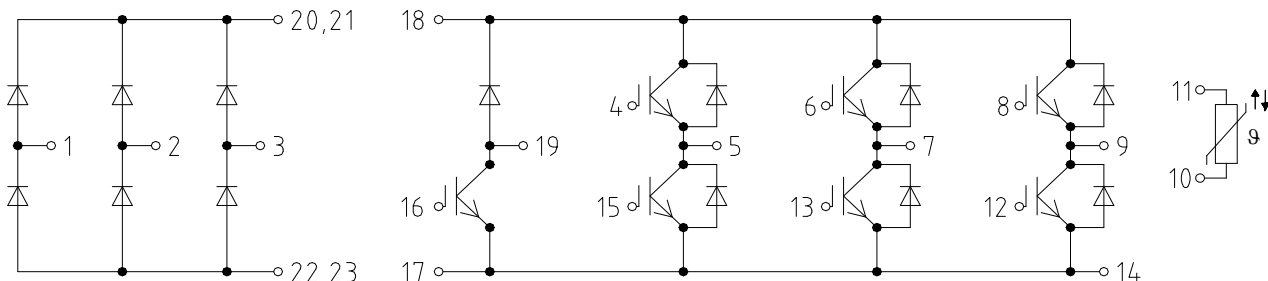
$R = f(T)$



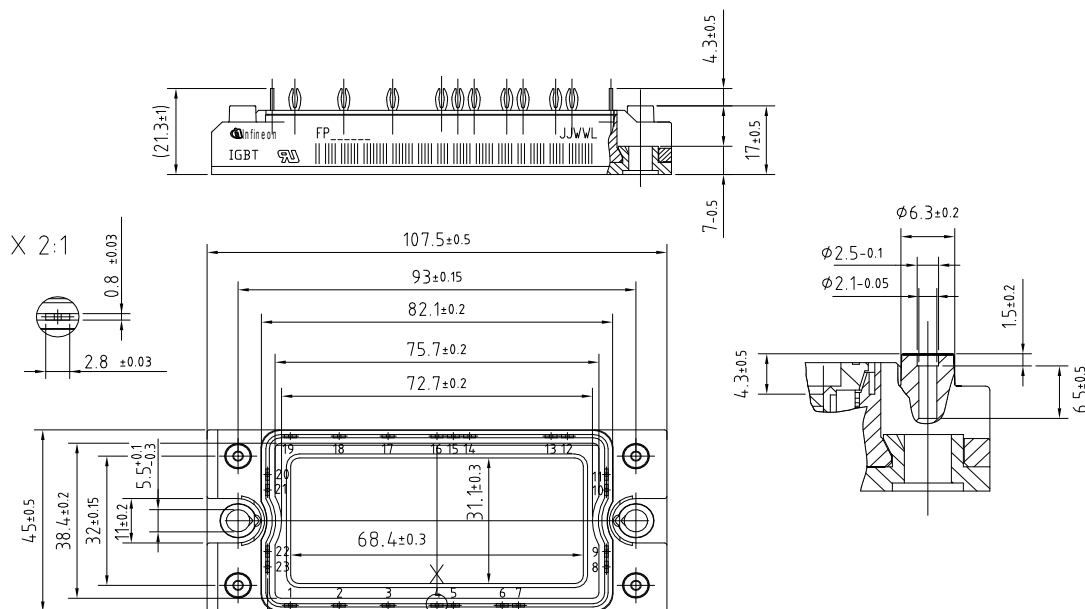
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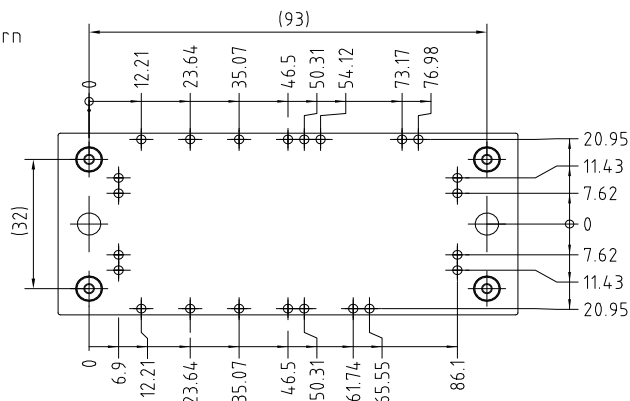
回路図 / circuit_diagram_headline



パッケージ概要 / package outlines



PCB hole pattern



- Tolerance of PCB hole pattern ± 0.1
- hole specifications see AN 2007-09
- Diameters of plated holes ϕ 2.14mm - 2.29mm
- Diameter of drill ϕ 2.35mm

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